

## 40V 3.5A DOUBLE POWER HALF BRIDGE

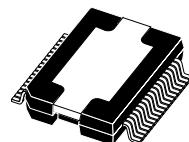
- MINIMUM INPUT OUTPUT PULSE WIDTH DISTORTION
- 200mΩ  $R_{dsON}$  COMPLEMENTARY DMOS OUTPUT STAGE
- CMOS COMPATIBLE LOGIC INPUTS
- THERMAL PROTECTION
- THERMAL WARNING OUTPUT
- UNDER VOLTAGE PROTECTION

### DESCRIPTION

STA501 is a monolithic dual half bridge stage in Multipower BCD Technology.

The device is particularly designed to make the output stage of a mono All-Digital High Efficiency

### MULTIPOWER BCD TECHNOLOGY

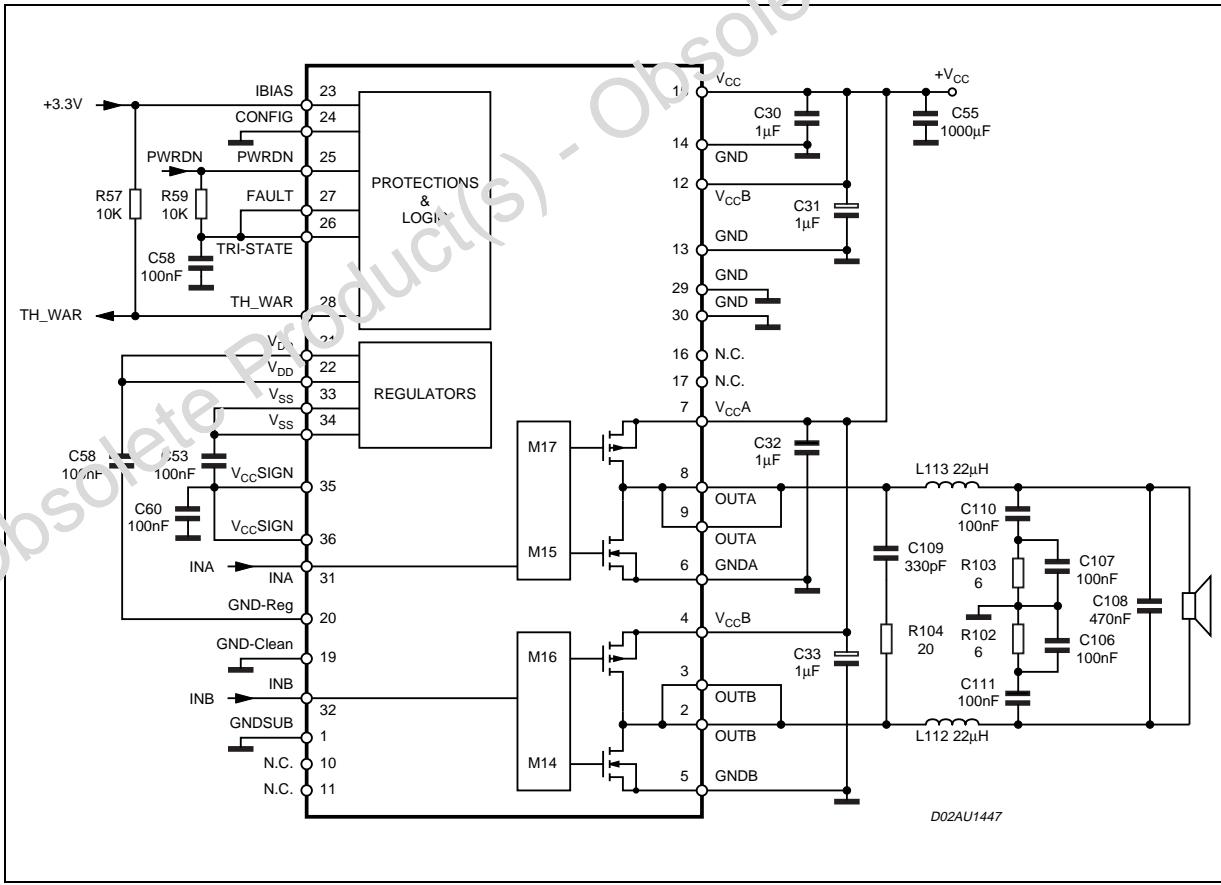


PowerSO36

ORDERING NUMBER: STA501

(DDX™) amplifier capable to deliver 50W @ THD = 10% at  $V_{cc}$  30V output power on  $8\Omega$  load. The input pins have threshold proportional to Ibias pin voltage.

### AUDIO APPLICATION CIRCUIT



## STA501

### PIN FUNCTION

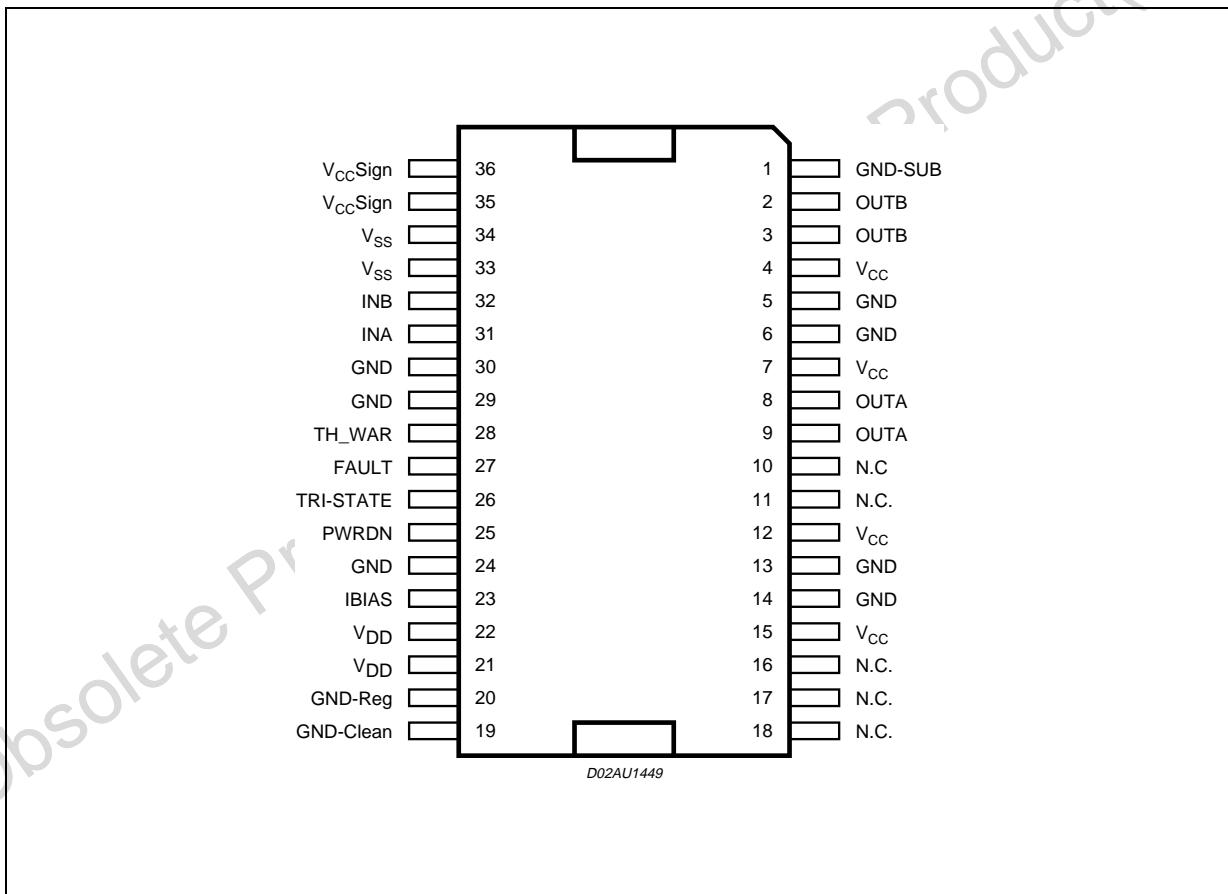
N°	Pin	Description
1	GND-SUB	Substrate ground
35 ; 36	Vcc Sign	Signal Positive Supply
15	Vcc	Positive Supply
12	Vcc	Positive Supply
7	Vcc	Positive Supply
4	Vcc	Positive Supply
14	GND	Negative Supply
13	GND	Negative Supply
6	GND	Negative Supply
5	GND	Negative Supply
16 ; 17	N.C.	
10 ; 11	N.C.	
8 ; 9	OUTA	Output half bridge
2 ; 3	OUTB	Output half bridge
29	GND	
30	GND	
31	INA	Input of half bridge
32	INB	Input of half bridge
21 ; 22	Vdd	5V Regulator referred to ground
33 ; 34	Vss	5V Regulator referred to +Vcc
25	PWRDN	Stand-by pin
26	TRI-STATE	Hi-Z pin
27	FAULT	Fault pin advisor
24	GND	
28	TH-WAR	Thermal warning advisor
19	GND-clean	Logical ground
23	IBIAS	High logical state setting voltage
18	NC	Not connected
20	GND-Reg	Ground for regulator Vdd

## FUNCTIONAL PIN STATUS

PIN NAME	Logical value	IC -STATUS
FAULT	0	Fault detected (Short circuit, or Thermal ..)
FAULT *	1	Normal Operation
TRI-STATE	0	All powers in Hi-Z state
TRI-STATE	1	Normal operation
PWRDN	0	Low absorpion
PWRDN	1	Normal operation
THWAR	0	Temperature of the IC =130C
THWAR*	1	Normal operation

\* : The pin is open collector. To have the high logic value, it needs to be pulled up by a resistor.

## PIN CONNECTION



**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
$V_{CE}$	DC Supply Voltage (Pin 4,7,12,15)	40	V
$V_{max}$	Maximum Voltage on pins 23 to 32	5.5	V
$T_{op}$	Operating Temperature Range	0 to 70	°C
$T_{stg}, T_j$	Storage and Junction Temperature	-40 to 150	°C

**THERMAL DATA**

Symbol	Parameter	Min.	Typ.	Max.	Unit
$T_{j-case}$	Thermal Resistance Junction to Case (thermal pad)			2.5	°C/W
$T_{jSD}$	Thermal shut-down junction temperature		150		°C
$T_{warn}$	Thermal warning temperature		130		°C
$t_{hSD}$	Thermal shut-down hysteresis		25		°C

**ELECTRICAL CHARACTERISTICS** ( $I_{bias} = 3.3V$ ;  $V_{cc} = 30V$ ;  $T_{amb} = 25°C$  unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$R_{dsON}$	Power Pchannel/Nchannel MOSFET $R_{dsON}$	$I_d=1A$		200	270	$m\Omega$
$I_{dss}$	Power Pchannel/Nchannel leakage $I_{dss}$	$V_{cc}=35V$			50	$\mu A$
$g_N$	Power Pchannel $R_{dsON}$ Matching	$I_d=1A$	95			%
$g_P$	Power Nchannel $R_{dsON}$ Matching	$I_d=1A$	95			%
$Dt_s$	Low current Dead Time (static)	see test circuit no. 1; see fig. 1		10	20	ns
$Dt_d$	High current Dead Time (dynamic)	$L=22\mu H$ ; $C = 470nF$ ; $R_L = 8 \Omega$ $I_d=3.5A$ ; see fig. 3			50	ns
$t_d ON$	Turn-on delay time	Resistive load			100	ns
$t_d OFF$	Turn-off delay time	Resistive load			100	ns
$t_r$	Rise time	Resistive load			25	ns
$t_f$	Fall time	Resistive load; as fig. 1			25	ns
$V_{cc}$	Supply voltage operating voltage		10		36	V
$V_{IN-H}$	High level input voltage				$I_{bias}/2 +300mV$	V
$V_{IN-L}$	Low level input voltage		$I_{bias}/2 -300mV$			V
$I_{IN-H}$	Hi level Input current	Pin voltage = $I_{bias}$		1		$\mu A$

**ELECTRICAL CHARACTERISTICS (continued)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I <sub>IN-L</sub>	Low level input current	Pin voltage = 0.3V		1		µA
I <sub>PWRDN-H</sub>	Hi level PWRDN pin input current	I <sub>bias</sub> = 3.3V		35		µA
V <sub>L</sub>	Low logical state voltage VL (pin PWRDN, TRISTATE) (note 1)	I <sub>bias</sub> = 3.3V	0.8			V
V <sub>H</sub>	High logical state voltage VH (pin PWRDN, TRISTATE) (note 1)	I <sub>bias</sub> = 3.3V			1.7	V
I <sub>VCC-PWRDN</sub>	Supply Current from Vcc in Power Down	PWRDN = 0			3	mA
I <sub>FAULT</sub>	Output Current pins FAULT -TH-WARN when FAULT CONDITIONS	V <sub>pin</sub> = 3.3V		1		mA
I <sub>VCC-hiz</sub>	Supply current from Vcc in Tri-state	V <sub>cc</sub> =30V; Tri-state=0		22		mA
I <sub>VCC</sub>	Supply current from Vcc in operation (both channel switching)	Input pulse width = 50% Duty; Switching Frequency = 384Khz; No LC filters;		50		mA
I <sub>out-sh</sub>	Overcurrent protection threshold (short circuit current limit)		3.5	6	8	A
V <sub>UV</sub>	Undervoltage protection threshold			7		V
t <sub>pw-min</sub>	Output minimum pulse width	No Load	70		150	ns

Notes: 1. The following table explains the VL, VH variation with Ibias

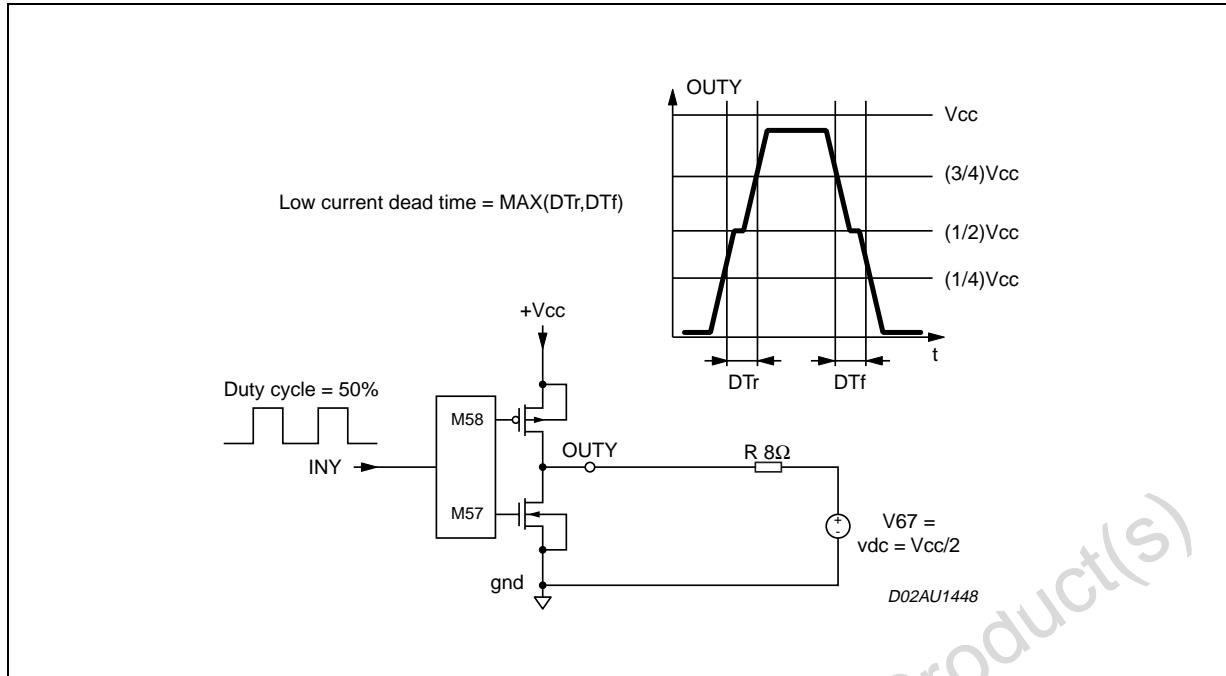
Ibias	VLmin	VHmax	Unit
2.7	0.7	1.5	V
3.3	0.8	1.7	V
5	0.85	1.85	V

**LOGIC TRUTH TABLE (see fig. 2)**

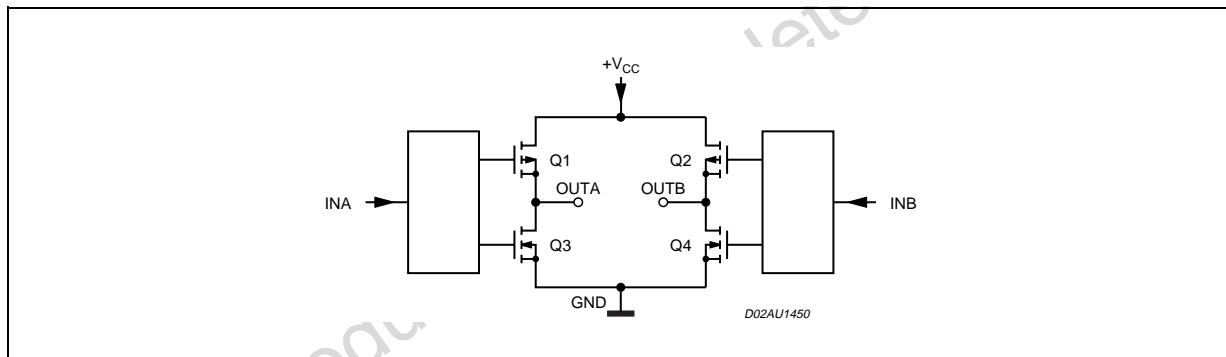
TRI-STATE	INA	INB	Q1	Q2	Q3	Q4	OUTPUT MODE
0	x	x	OFF	OFF	OFF	OFF	Hi-Z
1	0	0	OFF	OFF	ON	ON	DUMP
1	0	1	OFF	ON	ON	OFF	NEGATIVE
1	1	0	ON	OFF	OFF	ON	POSITIVE
1	1	1	ON	ON	OFF	OFF	Not used

## STA501

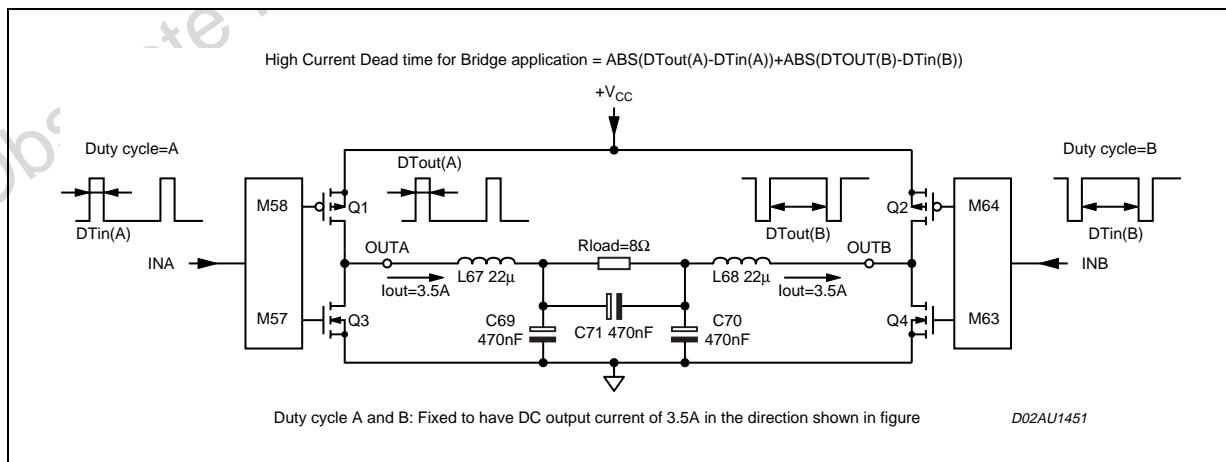
**Figure 1. Test Circuit.**



**Figure 2.**



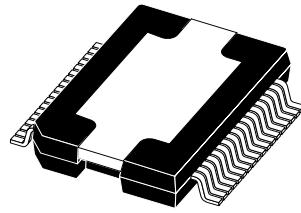
**Figure 3.**



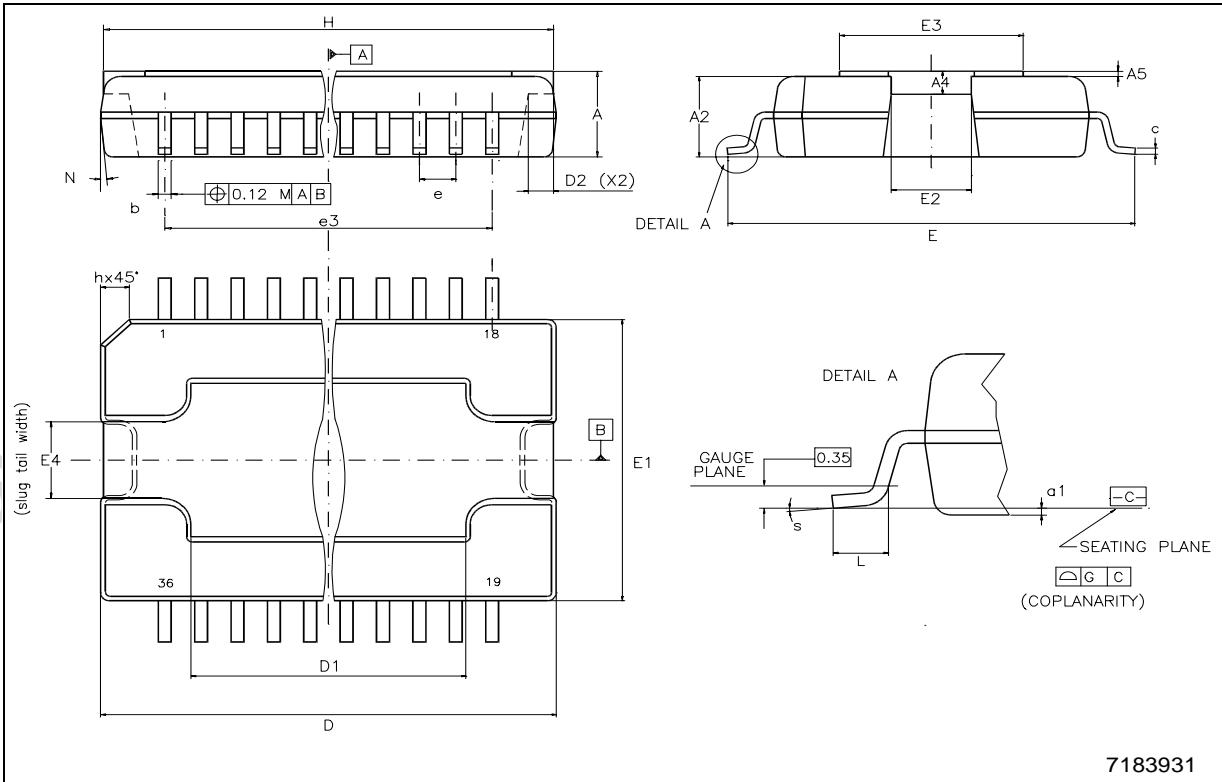
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	3.25		3.5	0.128		0.138
A2			3.3			0.13
A4	0.8		1	0.031		0.039
A5		0.2			0.008	
a1	0		0.075	0		0.003
b	0.22		0.38	0.008		0.015
c	0.23		0.32	0.009		0.012
D	15.8		16	0.622		0.630
D1	9.4		9.8	0.37		0.38
D2		1			0.039	
E	13.9		14.5	0.547		0.57
E1	10.9		11.1	0.429		0.437
E2			2.9			0.114
E3	5.8		6.2	0.228		0.244
E4	2.9		3.2	0.114		1.259
e		0.65			0.026	
e3		11.05			0.435	
G	0		0.075	0		0.003
H	15.5		15.9	0.61		0.625
h			1.1			0.043
L	0.8		1.1	0.031		0.043
N			10° (max)			
S			8° (max)			

(1) "D and E1" do not include mold flash or protusions.  
Mold flash or protusions shall not exceed 0.15mm (0.006")  
(2) No intrusion allowed inwards the leads.

## OUTLINE AND MECHANICAL DATA



## PowerSO36 (SLUG UP)



7183931

Obsolete Product(s) - Obsolete Product(s)

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics.  
All other names are the property of their respective owners

© 2003 STMicroelectronics - All rights reserved

**STMicroelectronics GROUP OF COMPANIES**

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -  
Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States  
[www.st.com](http://www.st.com)